NCV8440, NCV8440A

Protected Power MOSFET

2.6 A, 52 V, N−Channel, Logic Level, Clamped MOSFET w/ ESD Protection

Features

- Diode Clamp Between Gate and Source
- ESD Protection − Human Body Model 5000 V
- Active Over−Voltage Gate to Drain Clamp
- Scalable to Lower or Higher $R_{DS(on)}$
- Internal Series Gate Resistance
- These are Pb−Free Devices

Benefits

- High Energy Capability for Inductive Loads
- Low Switching Noise Generation

Applications

- Automotive and Industrial Markets:
  Solenoid Drivers, Lamp Drivers, Small Motor Drivers
- NCV Prefix for Automotive and Other Applications Requiring Site and Control Changes

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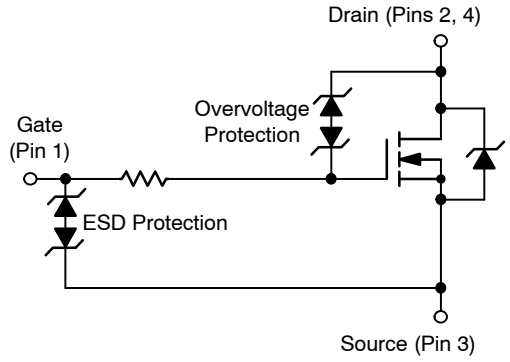
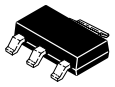
V_{DSS} (Clamped)	$R_{DS(ON)}$ TYP	I_D MAX
52 V	95 mΩ @ 10 V	2.6 A

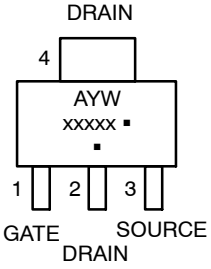




SOT−223
CASE 318E
STYLE 3

1 = Gate
2 = Drain
3 = Source

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
xxxxx = V8440 or 8440A
▪ = Pb−Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 8 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Rating	Symbol	Value	Unit
Drain−to−Source Voltage Internally Clamped	V_{DSS}	52−59	V
Gate−to−Source Voltage − Continuous	V_{GS}	±15	V
Drain Current − Continuous @ T_A = 25°C − Single Pulse (t_p = 10 μs) (Note 1)	I_D I_{DM}	 2.6 10	A
Total Power Dissipation @ T_A = 25°C (Note 1)	P_D	1.69	W
Operating and Storage Temperature Range	T_J, T_{stg}	−55 to 150	°C
Single Pulse Drain−to−Source Avalanche Energy (V_{DD} = 50 V, $I_{D(pk)}$ = 1.17 A, V_{GS} = 10 V, L = 160 mH, R_G = 25 Ω)	E_{AS}	110	mJ
Load Dump Voltage (V_{GS} = 0 and 10 V, R_I = 2.0 Ω, R_L = 9.0 Ω, td = 400 ms)	V_{LD}	60	V
Thermal Resistance, Junction−to−Ambient (Note 1) Junction−to−Ambient (Note 2)	 $R_{\theta JA}$ $R_{\theta JA}$	 74 169	°C/W
Maximum Lead Temperature for Soldering Purposes, 1/8″ from Case for 10 Seconds	T_L	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. When surface mounted to a FR4 board using 1″ pad size, (Cu area 1.127 in^2).
2. When surface mounted to a FR4 board using minimum recommended pad size, (Cu area 0.412 in^2).

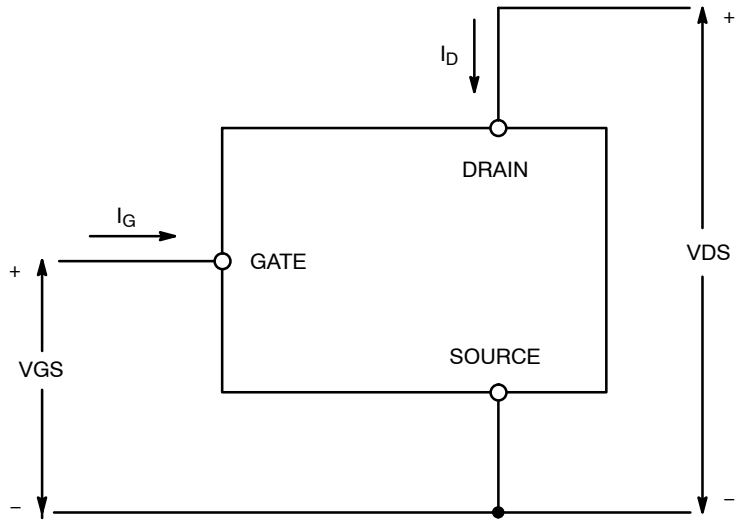


Figure 1. Voltage and Current Convention

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain−to−Source Breakdown Voltage (Note 3) (V_{GS} = 0 V, I_D = 1.0 mA, T_J = 25°C) (V_{GS} = 0 V, I_D = 1.0 mA, T_J = −40°C to 125°C) (Note 4) Temperature Coefficient (Negative)	$V_{(BR)DSS}$	 52 50.8	 55 54 −9.3	 59 59.5	 V V mV/°C
Zero Gate Voltage Drain Current (V_{DS} = 40 V, V_{GS} = 0 V) (V_{DS} = 40 V, V_{GS} = 0 V, T_J = 125°C) (Note 4)	I_{DSS}			 10 25	μA
Gate−Body Leakage Current (V_{GS} = ±8 V, V_{DS} = 0 V) (V_{GS} = ±14 V, V_{DS} = 0 V)	I_{GSS}		 ±35	 ±10	μA
ON CHARACTERISTICS (Note 3)					
Gate Threshold Voltage (Note 3) (V_{DS} = V_{GS}, I_D = 100 μA) Threshold Temperature Coefficient (Negative)	$V_{GS(th)}$	1.1	1.5 −4.1	1.9	V mV/°C
Static Drain−to−Source On−Resistance (Note 3) (V_{GS} = 3.5 V, I_D = 0.6 A) (V_{GS} = 4.0 V, I_D = 1.5 A) (V_{GS} = 10 V, I_D = 2.6 A)	$R_{DS(on)}$		 135 150 95	 180 160 110	mΩ
Forward Transconductance (Note 3) (V_{DS} = 15 V, I_D = 2.6 A)	g_{FS}		3.8		Mhos
DYNAMIC CHARACTERISTICS					
Input Capacitance	C_{iss}		155		pF
Output Capacitance	C_{oss}		60		
Transfer Capacitance	C_{rss}		25		
Input Capacitance	C_{iss}		170		pF
Output Capacitance	C_{oss}		70		
Transfer Capacitance	C_{rss}		30		

V_{DS} = 35 V, V_{GS} = 0 V, f = 10 kHz

V_{DS} = 25 V, V_{GS} = 0 V, f = 10 kHz

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Not subject to production testing.
5. Switching characteristics are independent of operating junction temperatures.

MOSFET ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic		Symbol	Min	Typ	Max	Unit
SWITCHING CHARACTERISTICS (Note 5)						
Turn−On Delay Time	V_{GS} = 4.5 V, V_{DD} = 40 V, I_D = 2.6 A, R_D = 15.4 Ω	$t_{d(on)}$		375		ns
Rise Time		t_r		1525		
Turn−Off Delay Time		$t_{d(off)}$		1530		
Fall Time		t_f		1160		
Turn−On Delay Time	V_{GS} = 4.5 V, V_{DD} = 40 V, I_D = 1.0 A, R_D = 40 Ω	$t_{d(on)}$		325		ns
Rise Time		t_r		1275		
Turn−Off Delay Time		$t_{d(off)}$		1860		
Fall Time		t_f		1150		
Turn−On Delay Time	V_{GS} = 10 V, V_{DD} = 15 V, I_D = 2.6 A, R_D = 5.8 Ω	$t_{d(on)}$		190		ns
Rise Time		t_r		710		
Turn−Off Delay Time		$t_{d(off)}$		2220		
Fall Time		t_f		1180		
Gate Charge	V_{GS} = 4.5 V, V_{DS} = 40 V, I_D = 2.6 A (Note 3)	Q_T		4.5		nC
		Q_1		0.9		
		Q_2		2.6		
Gate Charge	V_{GS} = 4.5 V, V_{DS} = 15 V, I_D = 1.5 A (Note 3)	Q_T		3.9		nC
		Q_1		1.0		
		Q_2		1.7		
SOURCE−DRAIN DIODE CHARACTERISTICS						
Forward On−Voltage	I_S = 2.6 A, V_{GS} = 0 V (Note 3) I_S = 2.6 A, V_{GS} = 0 V, T_J = 125°C	V_{SD}		0.81 0.66	1.5	V
Reverse Recovery Time	I_S = 1.5 A, V_{GS} = 0 V, dI_s/dt = 100 A/μs (Note 3)	t_{rr}		730		ns
		t_a		200		
		t_b		530		
Reverse Recovery Stored Charge		Q_{RR}		6.3		μC
ESD CHARACTERISTICS (Note 4)						
Electro−Static Discharge Capability	Human Body Model (HBM)	ESD	5000			V
	Machine Model (MM)		500			

3. Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.
4. Not subject to production testing.
5. Switching characteristics are independent of operating junction temperatures.

TYPICAL PERFORMANCE CURVES

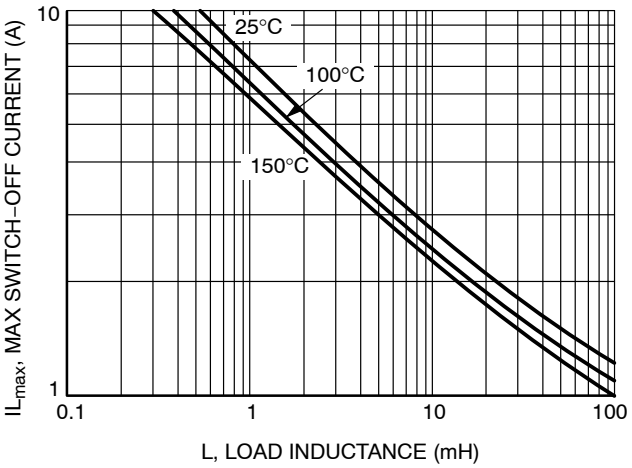


Figure 1. Single Pulse Maximum Switch−off Current vs. Load Inductance

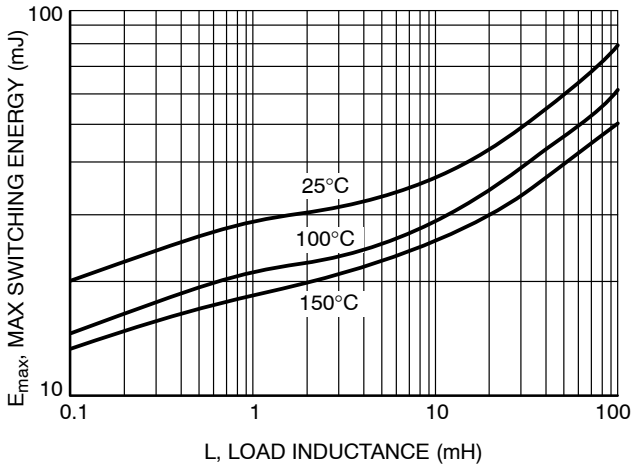


Figure 2. Single Pulse Maximum Switching Energy vs. Load Inductance

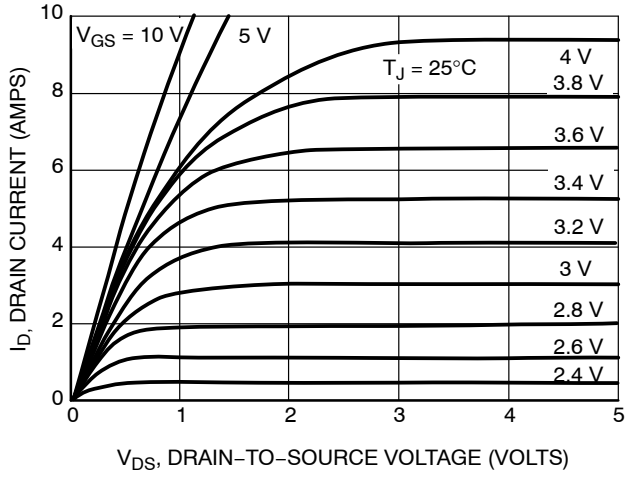


Figure 3. On−State Output Characteristics

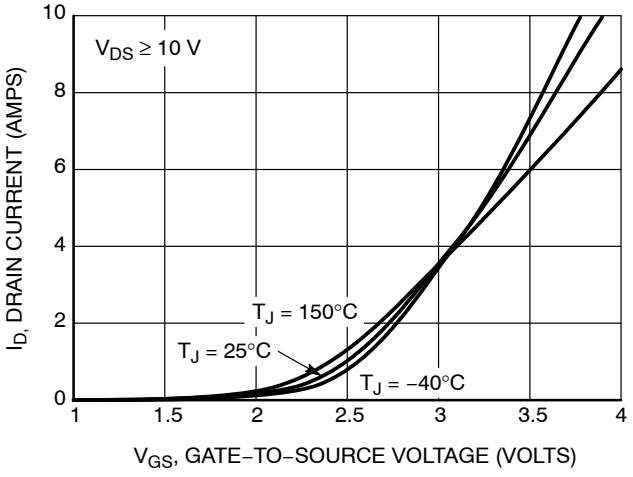


Figure 4. Transfer Characteristics

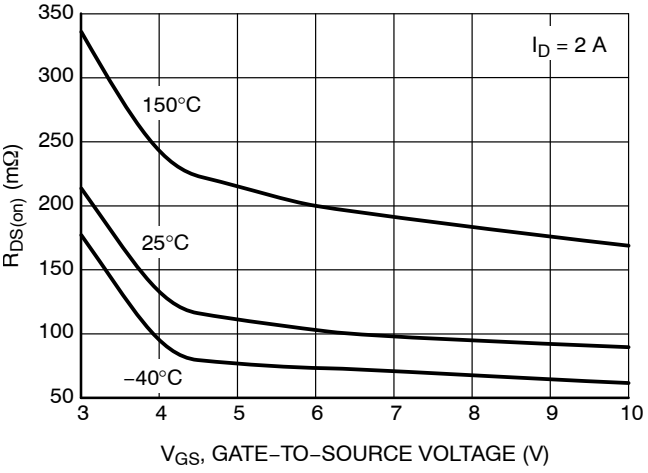


Figure 5. $R_{DS(on)}$ vs. Gate−Source Voltage

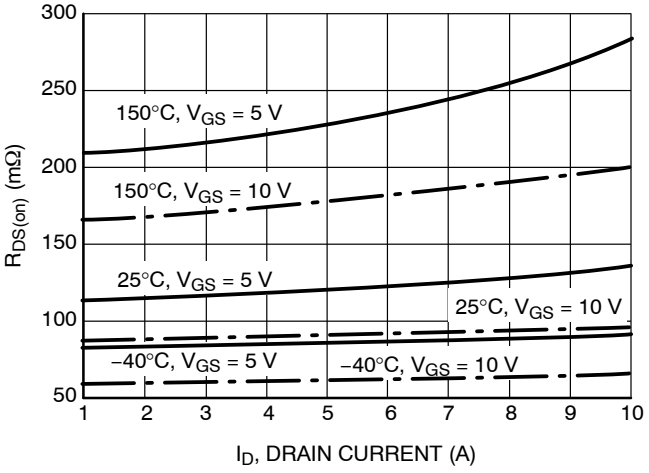


Figure 6. $R_{DS(on)}$ vs. Drain Current

TYPICAL PERFORMANCE CURVES

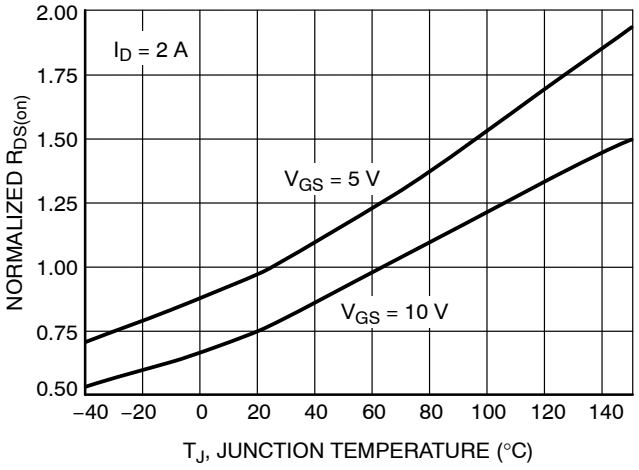


Figure 7. Normalized $R_{DS(on)}$ vs. Temperature

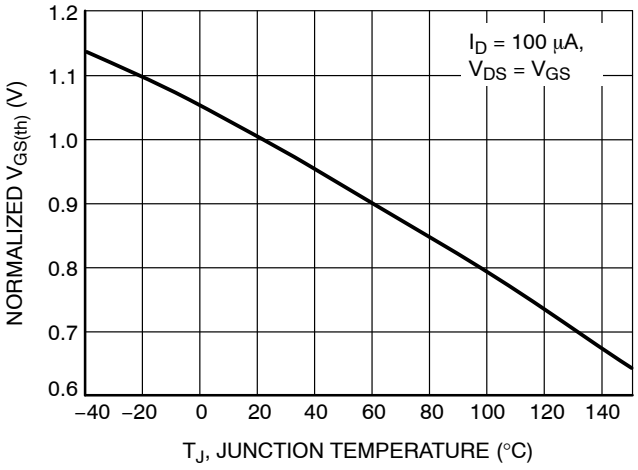


Figure 8. Normalized Threshold Voltage vs. Temperature

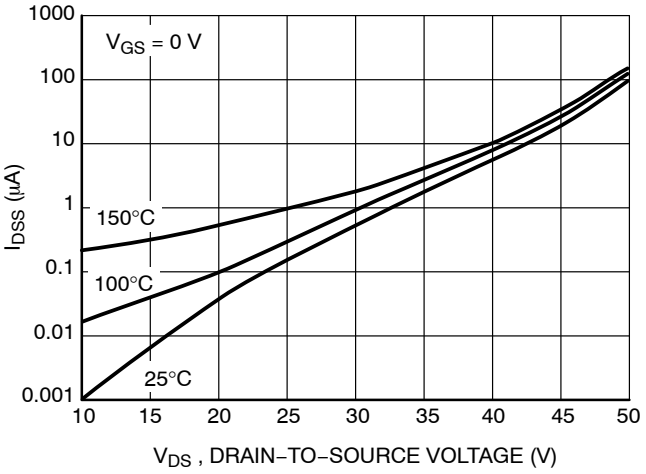


Figure 9. Drain−to−Source Leakage Current

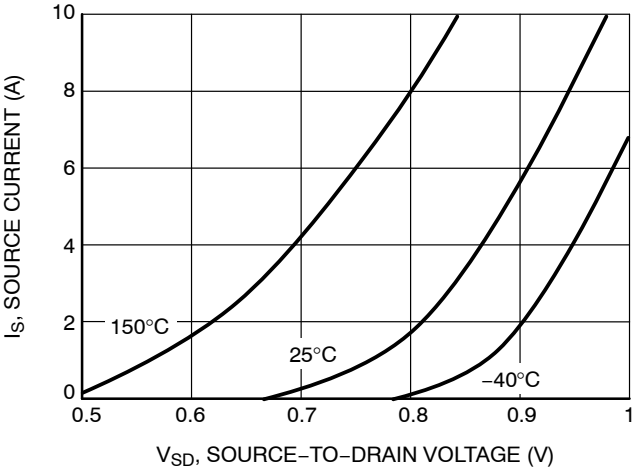


Figure 10. Source−Drain Diode Forward Characteristics

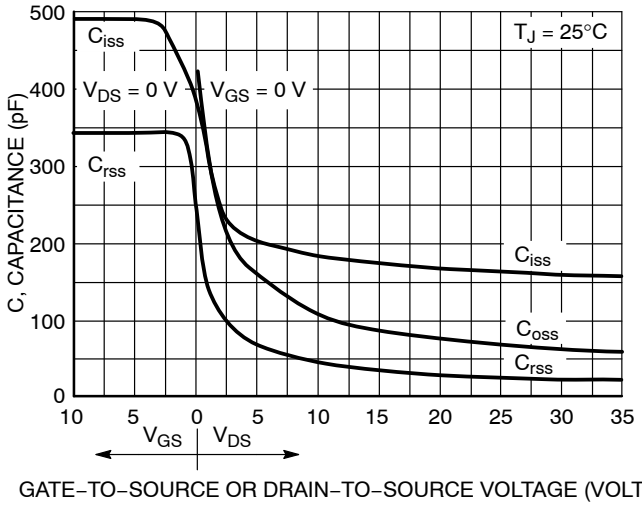


Figure 11. Capacitance Variation

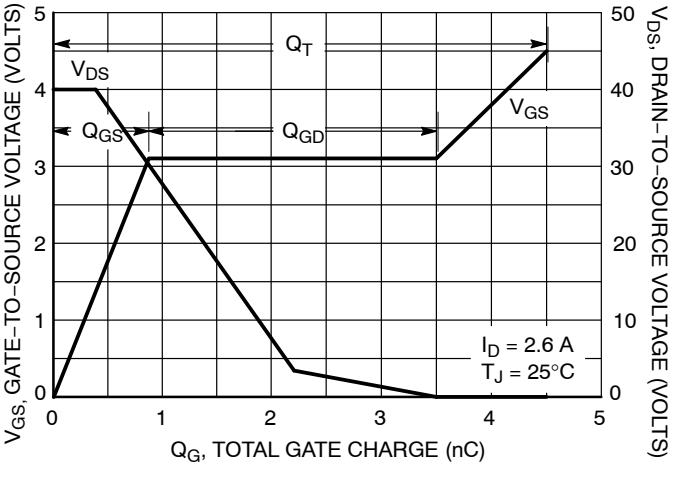


Figure 12. Gate−to−Source Voltage vs. Total Gate Charge

TYPICAL PERFORMANCE CURVES

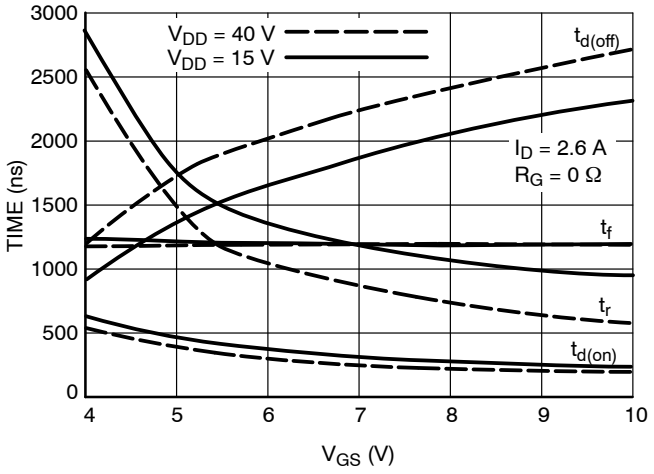


Figure 13. Resistive Load Switching Time vs. Gate−Source Voltage

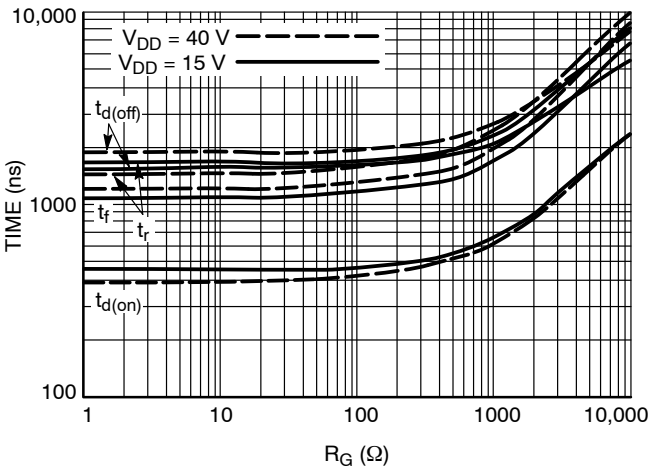


Figure 14. Resistive Load Switching Time vs. Gate Resistance (V_{GS} = 5 V, I_D = 2.6 A)

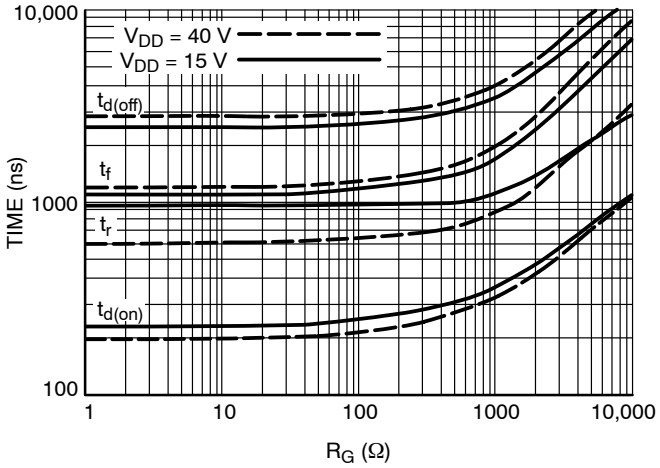


Figure 15. Resistive Load Switching Time vs. Gate Resistance (V_{GS} = 10 V, I_D = 2.6 A)

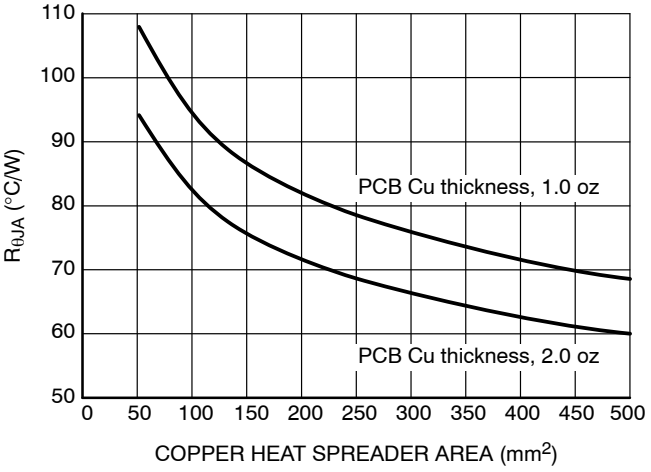


Figure 16. $R_{\theta JA}$ vs. Copper Area

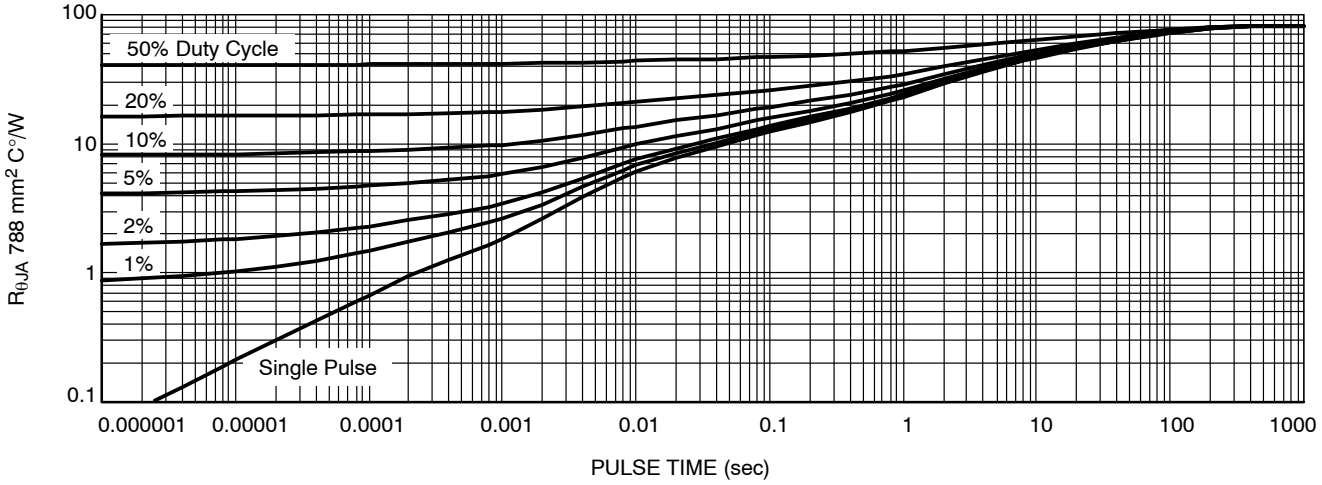


Figure 17. Transient Thermal Resistance

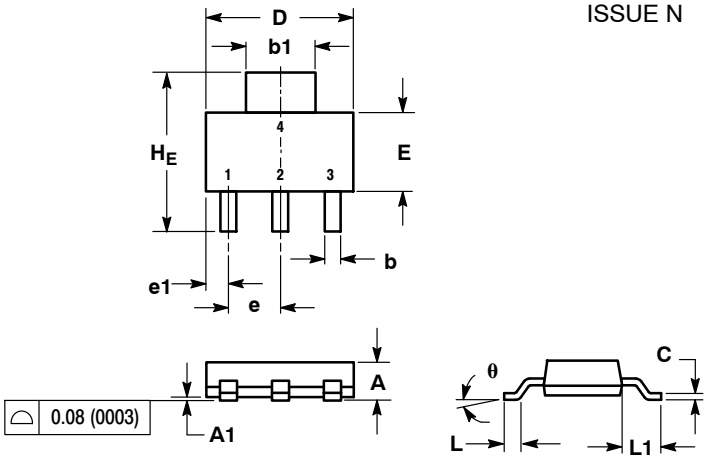
ORDERING INFORMATION

Device	Package	Shipping†
NCV8440STT1G	SOT−223 (Pb−Free)	1000 / Tape & Reel
NCV8440ASTT1G	SOT−223 (Pb−Free)	1000 / Tape & Reel
NCV8440STT3G	SOT−223 (Pb−Free)	4000 / Tape & Reel
NCV8440ASTT3G	SOT−223 (Pb−Free)	4000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

PACKAGE DIMENSIONS

SOT−223 (TO−261)
CASE 318E−04
ISSUE N

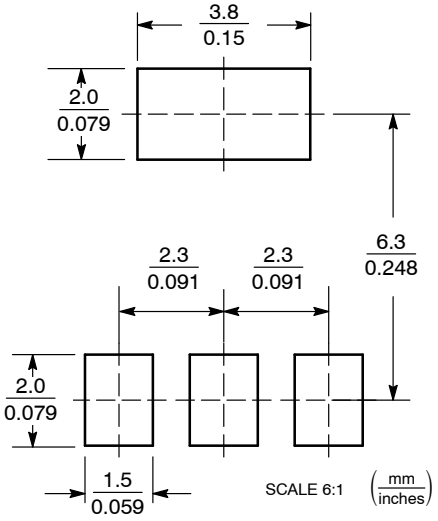


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	−−−	−−−	0.008	−−−	−−−
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	–	10°	0°	–	10°

STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative

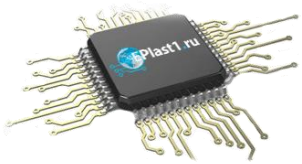
Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits,General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)
Факс: 8 (812) 320-02-42
Электронная почта: org@eplast1.ru
Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.